

Title of Change:	Hydrazine elimination in ON Semiconductor Niigata Co., Ltd., Japan (OSNC) and change of lead frame raw metal.					
Proposed first ship date:	24 May 2019					
Contact information:	Contact your local ON Semiconductor Sales Office or <yukio.kudo@onsemi.com></yukio.kudo@onsemi.com>					
Samples:	Contact your local ON Semiconductor Sales Office or < <u>PCN.samples@onsemi.com</u> > Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.					
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <satoru.fujinuma@onsemi.com></satoru.fujinuma@onsemi.com>					
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact < <u>PCN.Support@onsemi.com></u>					
Change Part Identification:	Date Code					
Change Category:	✓ Wafer Fab Change ✓ Assembly Change					
Change Sub-Category(s): Manufacturing Site Additi Manufacturing Site Transfer Manufacturing Process Ch Sites Affected: Description and Purpose: This Final notification announces	Sub-Category(s): Material Change Datasheet/Product Doc change anufacturing Site Addition Product specific change Shipping/Packaging/Marking anufacturing Process Change Other: Other: ffected: ON Semiconductor Sites: External Foundry/Subcon Sites: ON Niigata, Japan None					
The related products are transferred to a process that does not use Hydrazine on the same site ON Semiconductor Niigata, Japan (OSNC). In addition to change the lead frame raw material from C50710 to C19400.						
Change Point	Before Change Description	After Change Description				
Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=10)	N1 Fab (Minimum rule=0.8um, Class=10) AND N2 Fab (Minimum rule=0.25um, Class=1)				
Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)				
Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide				
Lead frame	Raw material of C50710	Raw material of C19400				



Reliability Data Summary:

QV DEVICE NAME : LB11870-TRM-E PACKAGE:HSSOP48(375mil)

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
тс	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
тнв	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

Electrical Characteristic Summary:

There is no change in the electrical performance. Datasheet specifications remain unchanged.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
LB11696V-W-AH	LB11870-TRM-E
LB11867FV-W-AH	LB11870-TRM-E
LB11867RV-W-AH	LB11870-TRM-E
LB8503V-W-AH	LB11870-TRM-E



Appendix A: Changed Products

Product	Customer Part Number	Qualification Vehicle
LB11696V-W-AH		LB11870-TRM-E
LB11867FV-W-AH		LB11870-TRM-E
LB11867RV-W-AH		LB11870-TRM-E
LB8503V-W-AH		LB11870-TRM-E